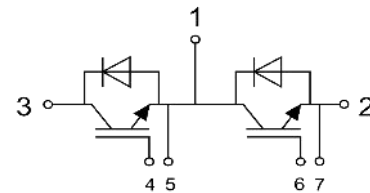


$V_{CES} = 1200V$

$I_C = 200A$ at $T_C = 80^\circ C$

$V_{CE(ON)} = 1.70V$ at $I_C = 200A$

**IGBT Half-Bridge
POWIR 62™ Package**



Applications:

- Industrial Motor Drive
- Uninterruptible Power Supply
- Welding and Cutting Machine
- Switched Mode Power Supply
- Induction Heating

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High Efficiency in a Wide Range of Applications
100% RBSOA Tested	Rugged Transient Performance
POWIR 62™ Package	Industry Standard
Lead Free	RoHS Compliant, Environmental Friendly

Base Part Number	Package Type	Standard Pack	Quantity	Orderable Part Number
IRG7U200HF12B	POWIR 62™	Box	45	IRG7U200HF12B

Absolute Maximum Ratings of IGBT

V_{CES}	Collector to Emitter Voltage	1200	V
V_{GES}	Continuous Gate to Emitter Voltage	±20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C$	200 A
		$T_C = 25^\circ C$	400 A
I_{CM}	Pulse Collector Current	$T_J = 175^\circ C$	400 A
P_D	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C, T_J = 175^\circ C$	1130 W
T_J	Maximum IGBT Junction Temperature	175	°C
T_{JOP}	Maximum Operating Junction Temperature Range	-40 to +150	°C
T_{stg}	Storage Temperature	-40 to +125	°C

Electrical Characteristics of IGBT at $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$V_{(BR)CES}$	Collector to Emitter Breakdown Voltage	1200			V	$V_{GE} = 0V, I_C = 2mA$	
$V_{GE(th)}$	Gate Threshold Voltage	3.4	4.2	4.9	V	$I_C = 10mA, V_{CE} = V_{GE}$	
$V_{CE(ON)}$	Collector to Emitter Saturation Voltage		1.70	2.00	V	$T_J = 25^\circ\text{C}$	$I_C = 200A, V_{GE} = 15V$
			1.90		V	$T_J = 125^\circ\text{C}$	
I_{CES}	Collector to Emitter Leakage Current			2	mA	$V_{GE} = 0V, V_{CE} = V_{CES}$	
I_{GES}	Gate to Emitter Leakage Current			400	nA	$V_{GE} = \pm 20V, V_{CE} = 0V$	
R_{Gint}	Internal Gate Resistance		1.25		Ω		

Switching Characteristics of IGBT

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$t_{d(on)}$	Turn-on Delay Time		1100		ns	$T_J = 25^\circ\text{C}$	$V_{CC}=600V, I_C = 200A, R_G = 15\Omega, V_{GE}=\pm 15V, \text{Inductive Load}$
			1080			$T_J = 125^\circ\text{C}$	
t_r	Rise Time		200		ns	$T_J = 25^\circ\text{C}$	
			205			$T_J = 125^\circ\text{C}$	
$t_{d(off)}$	Turn-off Delay Time		900		ns	$T_J = 25^\circ\text{C}$	
			950			$T_J = 125^\circ\text{C}$	
t_f	Fall Time		110		ns	$T_J = 25^\circ\text{C}$	
			140			$T_J = 125^\circ\text{C}$	
E_{on}	Turn-on Switching Loss		19.0		mJ	$T_J = 25^\circ\text{C}$	
			22.9			$T_J = 125^\circ\text{C}$	
E_{off}	Turn-off Switching Loss		15.2		mJ	$T_J = 25^\circ\text{C}$	
			19.8			$T_J = 125^\circ\text{C}$	
Q_g	Total Gate Charge		2100		nC	$T_J = 25^\circ\text{C}$	
C_{ies}	Input Capacitance		20.0		nF	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz, T_J = 25^\circ\text{C}$	
C_{oes}	Output Capacitance		1.08				
C_{res}	Reverse Transfer Capacitance		0.75				
RBSOA	Reverse Bias Safe Operating Area	Trapezoid				$I_C = 400A, V_{CC} = 960V, V_P = 1200V, R_G = 15\Omega, V_{GE} = +15V \text{ to } 0V, T_J = 150^\circ\text{C}$	

Absolute Maximum Ratings of Freewheeling Diode

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current, $T_C = 25^\circ\text{C}$	400	A
	Diode Continuous Forward Current, $T_C = 80^\circ\text{C}$	200	
I_{FM}	Pulse Diode Current	400	A

Electrical and Switching Characteristics of Freewheeling Diode

Parameter		Typ.	Max.	Unit	Test Conditions	
V_F	Forward Voltage	2.00	2.70	V	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$, $V_{GE} = 0\text{V}$
		2.20			$T_J = 125^\circ\text{C}$	
I_{rr}	Peak Reverse Recovery Current	65		A	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$, $di/dt = 960\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$
		105			$T_J = 125^\circ\text{C}$	
Q_{rr}	Reverse Recovery Charge	9.65		μC	$T_J = 25^\circ\text{C}$	
		21.80			$T_J = 125^\circ\text{C}$	
E_{rec}	Reverse Recovery Energy	3.20		mJ	$T_J = 25^\circ\text{C}$	
		8.40			$T_J = 125^\circ\text{C}$	

Module Characteristics

Parameter		Min.	Typ.	Max.	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted), $f = 50\text{Hz}$, 1minute			2500	V
$R_{\theta JC}$	Junction-to-Case (IGBT)		0.132		$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case (Diode)		0.204		$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)		0.1		$^\circ\text{C}/\text{W}$
M	Power Terminals Screw: M6	3.0		5.0	N·m
M	Mounting Screw: M6	4.0		6.0	N·m
G	Weight		230		g

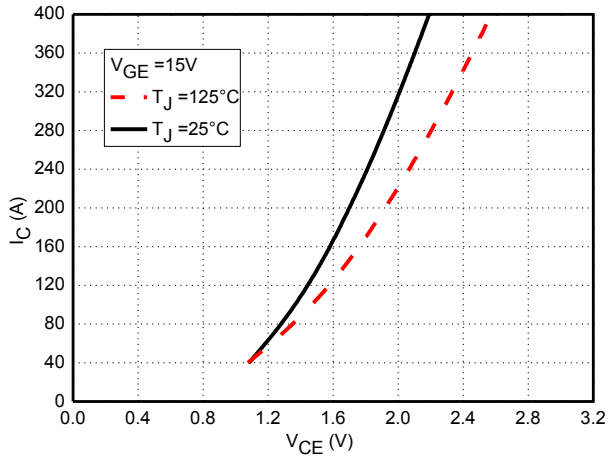


Fig.1 Typical IGBT Saturation Characteristics

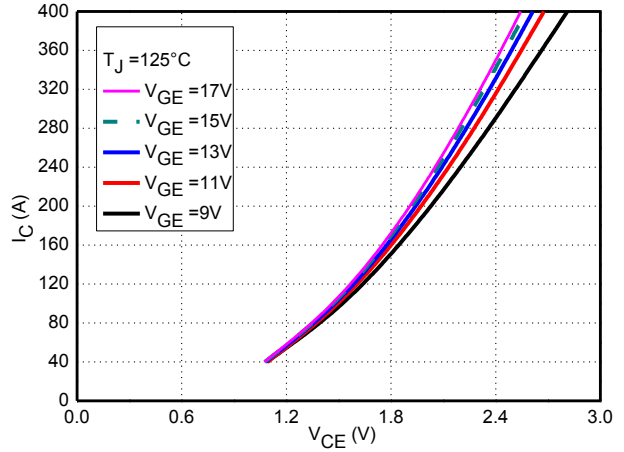


Fig.2 Typical IGBT Output Characteristics

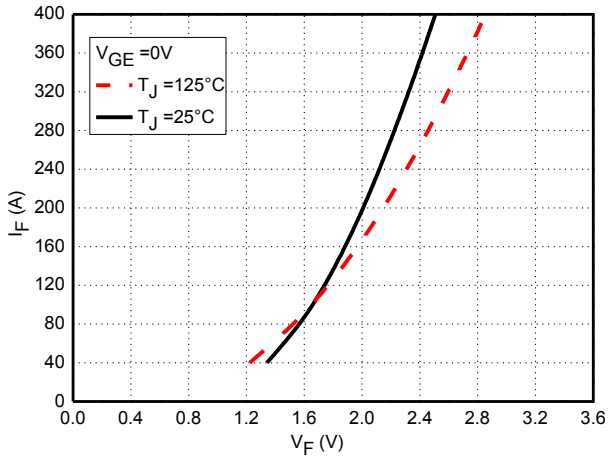


Fig.3 Typical Freewheeling Diode Characteristics

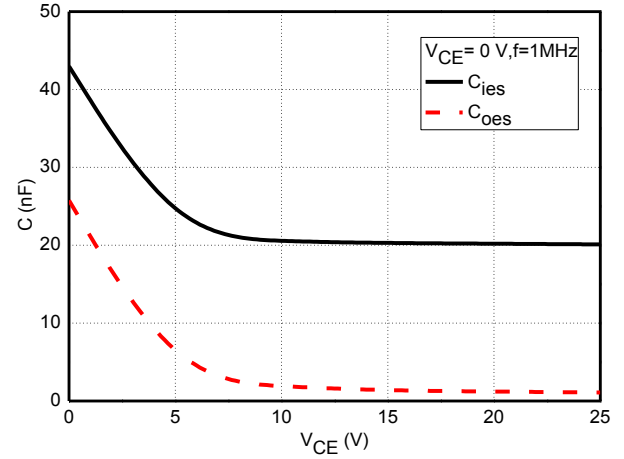


Fig. 4 Typical Capacitance Characteristics

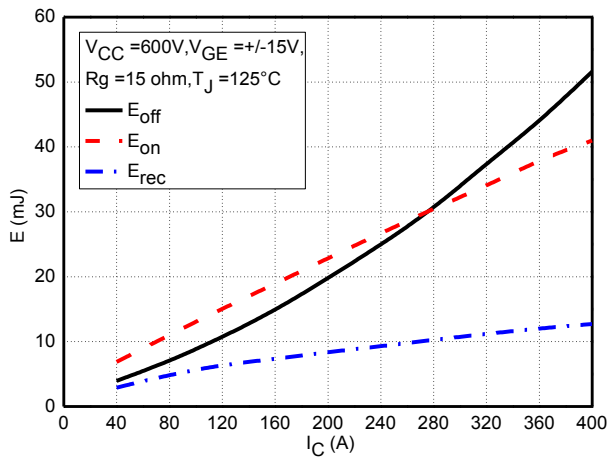


Fig.5 Typical Switching Loss vs. Collector Current

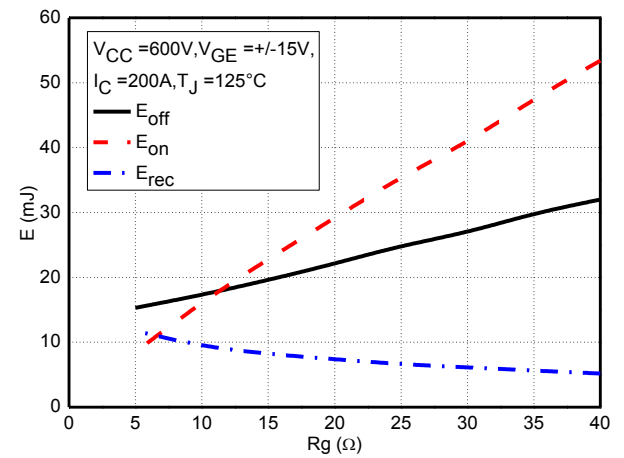


Fig.6 Typical Switching Loss vs. Gate Resistance

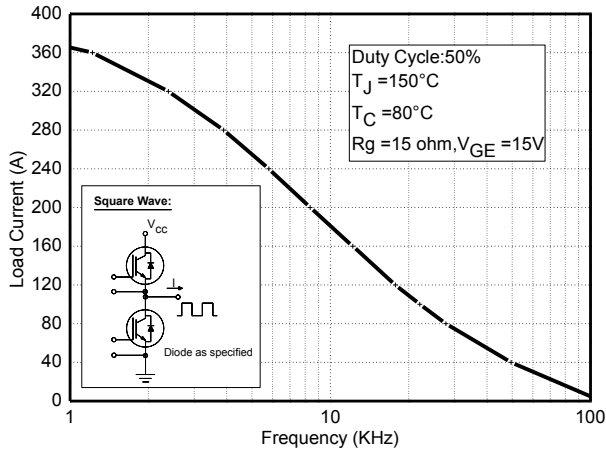


Fig.7 Typical Load Current vs. Frequency

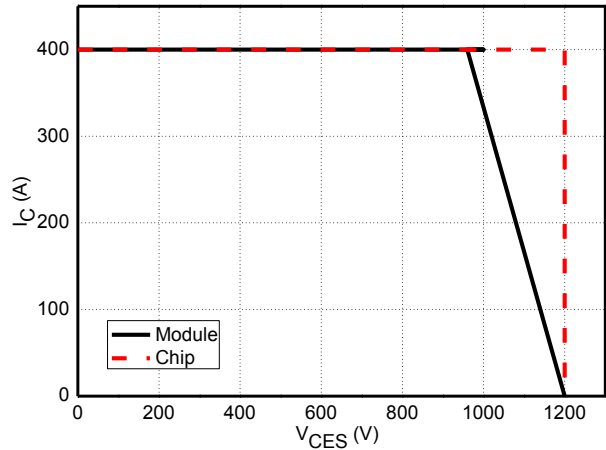


Fig.8 Reverse Bias Safe Operation Area (RBSOA)

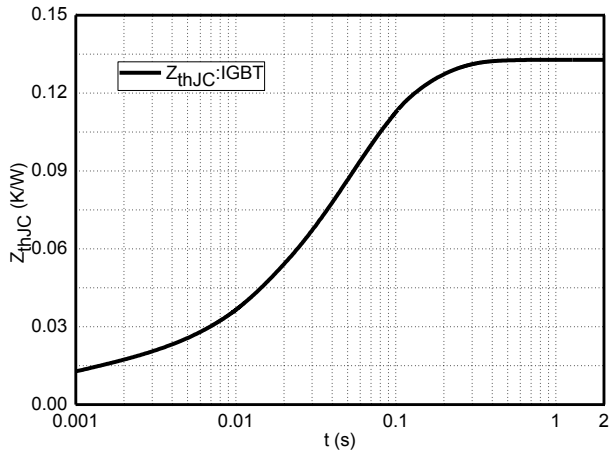


Fig.9 Typical Transient Thermal Impedance (IGBT)

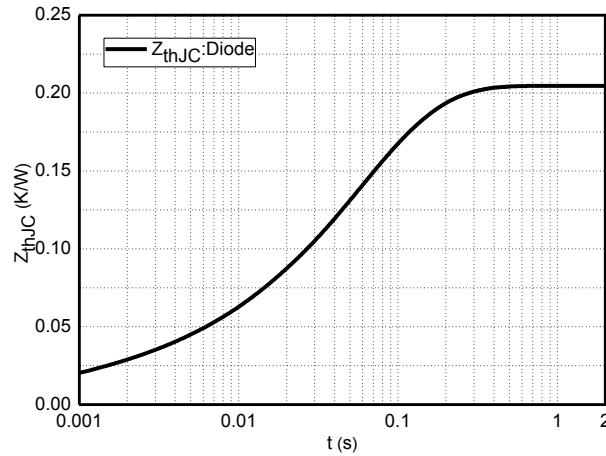


Fig.10 Typical Transient Thermal Impedance (Diode)

